2N4920G

Medium-Power Plastic PNP Silicon Transistors

These medium−power, high−performance plastic devices are designed for driver circuits, switching, and amplifier applications.

Features

- Low Saturation Voltage
- Excellent Power Dissipation Due to Thermopad™ Construction
- Excellent Safe Operating Area
- Complement to NPN 2N4921G, 2N4922G, 2N4923G
- This Device is Pb−Free and is RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CEO}	80	Vdc
Collector − Base Voltage	V_{CBO}	80	Vdc
Emitter − Base Voltage	V_{EBO}	5.0	Vdc
Collector Current − Continuous (Note 1)	I_C	1.0	Adc
Collector Current − Peak	I_{CM}	3.0	Adc
Base Current	I_B	1.0	Adc
Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	30 0.24	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The 1.0 A max I_C value is based upon JEDEC current gain requirements. The 3.0 A max value is based upon actual current−handling capability of the device (See Figure 5).

THERMAL CHARACTERISTICS (Note 2)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	4.16	°C/W

2. Recommend use of thermal compound for lowest thermal resistance.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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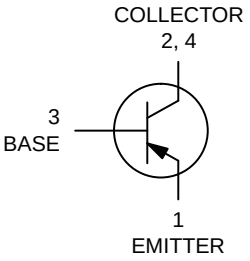
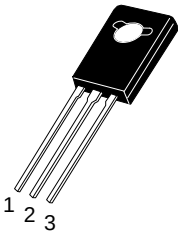
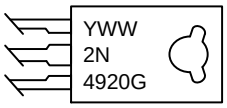
3.0 A, 40−80 V, 30 W GENERAL PURPOSE POWER TRANSISTORS





TO−225
CASE 77−09
STYLE 1

MARKING DIAGRAM



Y = Year
WW = Work Week
2N4920 = Specific Device Code
G = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping
2N4920G	TO−225 (Pb−Free)	500 Unit / Bulk

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector−Emitter Sustaining Voltage (Note 3) (I_C = 0.1 Adc, I_B = 0)	$V_{CEO(sus)}$	80	–	Vdc
Collector Cutoff Current (V_{CE} = 40 Vdc, I_B = 0)	I_{CEO}	–	0.5	mAdc
Collector Cutoff Current (V_{CE} = Rated V_{CEO}, $V_{BE(off)}$ = 1.5 Vdc) (V_{CE} = Rated V_{CEO}, $V_{BE(off)}$ = 1.5 Vdc, T_C = 125°C	I_{CEX}	– –	0.1 0.5	mAdc
Collector Cutoff Current (V_{CB} = Rated V_{CB}, I_E = 0)	I_{CBO}	–	0.1	mAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)	I_{EBO}	–	1.0	mAdc
ON CHARACTERISTICS				
DC Current Gain (Note 3) (I_C = 50 mAdc, V_{CE} = 1.0 Vdc) (I_C = 500 mAdc, V_{CE} = 1.0 Vdc) (I_C = 1.0 Adc, V_{CE} = 1.0 Vdc)	h_{FE}	 40 30 10	 – 150 –	–
Collector−Emitter Saturation Voltage (Note 3) (I_C = 1.0 Adc, I_B = 0.1 Adc)	$V_{CE(sat)}$	–	0.6	Vdc
Base−Emitter Saturation Voltage (Note 3) (I_C = 1.0 Adc, I_B = 0.1 Adc)	$V_{BE(sat)}$	–	1.3	Vdc
Base−Emitter On Voltage (Note 3) (I_C = 1.0 Adc, V_{CE} = 1.0 Vdc)	$V_{BE(on)}$	–	1.3	Vdc
SMALL−SIGNAL CHARACTERISTICS				
Current−Gain − Bandwidth Product (I_C = 250 mAdc, V_{CE} = 10 Vdc, f = 1.0 MHz)	f_T	3.0	–	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{ob}	–	100	pF
Small−Signal Current Gain (I_C = 250 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	25	–	–

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: PW ≈ 300 μs, Duty Cycle ≈ 2.0%

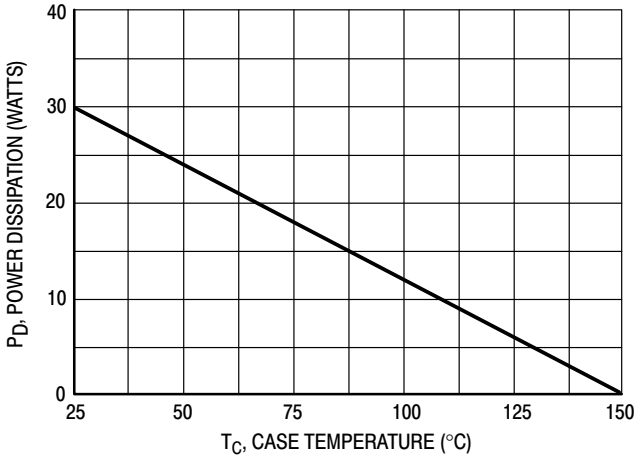


Figure 1. Power Derating

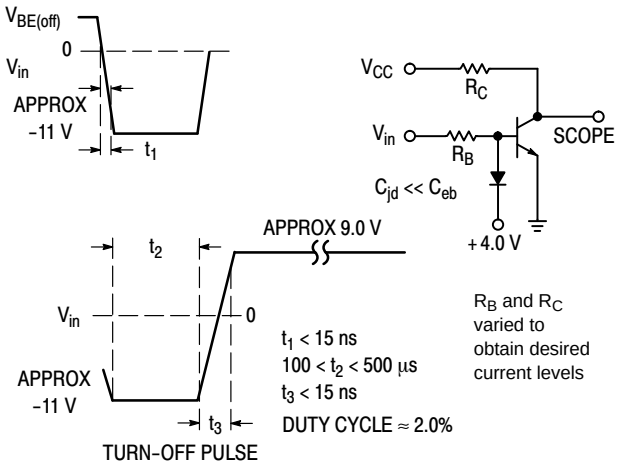


Figure 2. Switching Time Equivalent Test Circuit

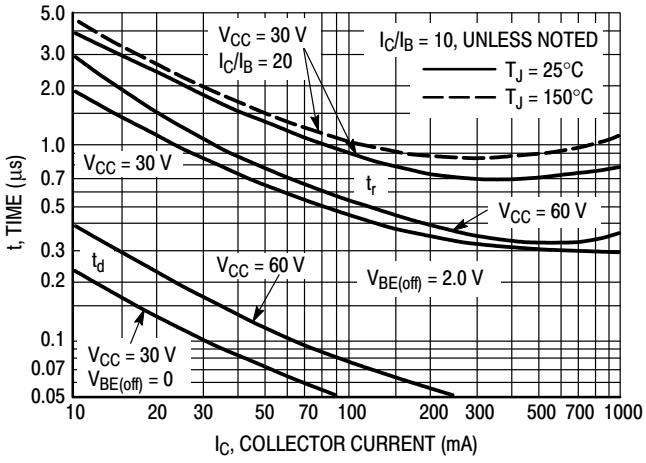


Figure 3. Turn−On Time

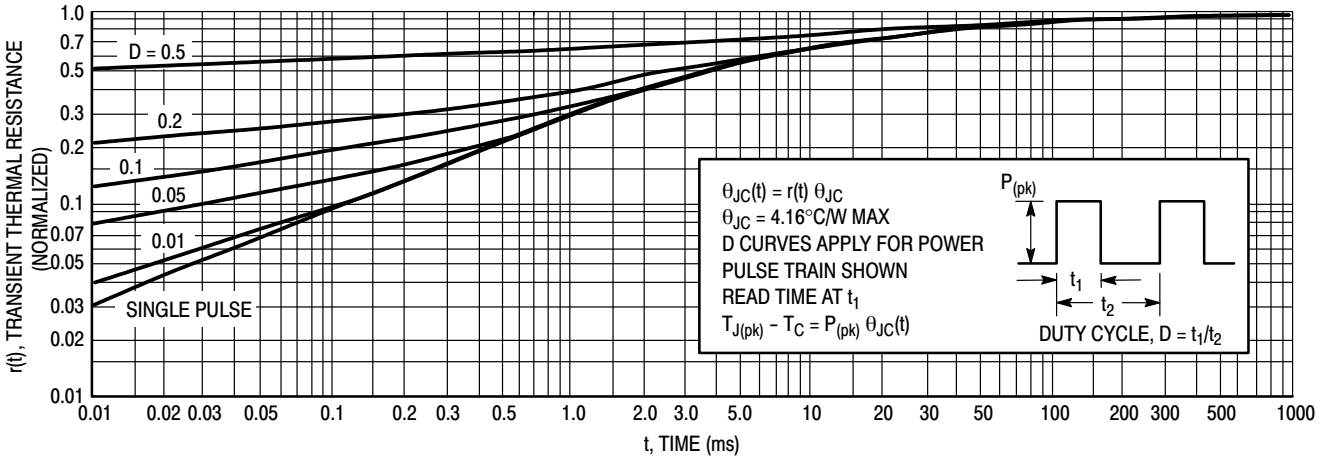


Figure 4. Thermal Response

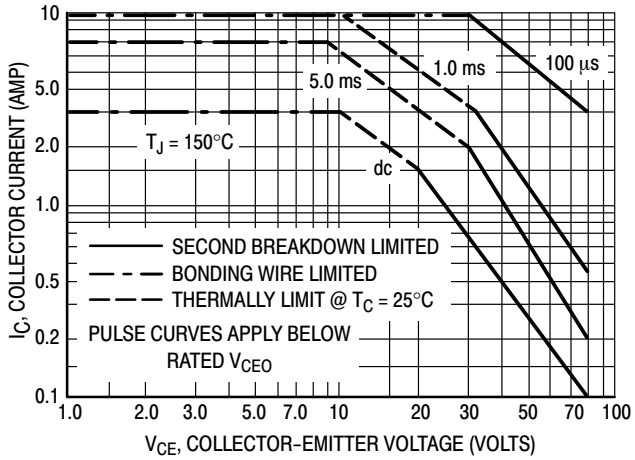


Figure 5. Active−Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ operation i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150°C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150°C$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

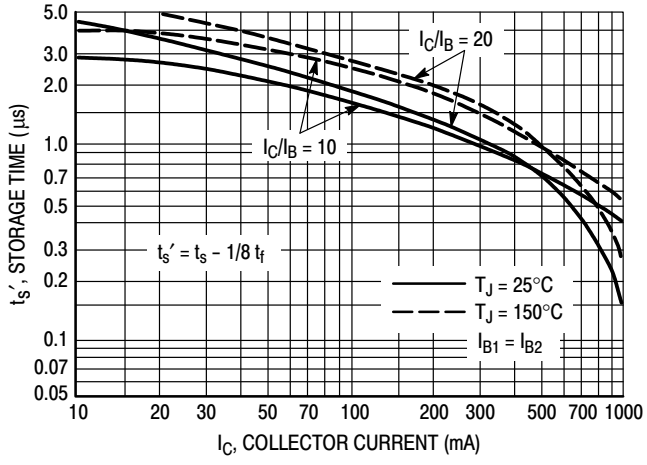


Figure 6. Storage Time

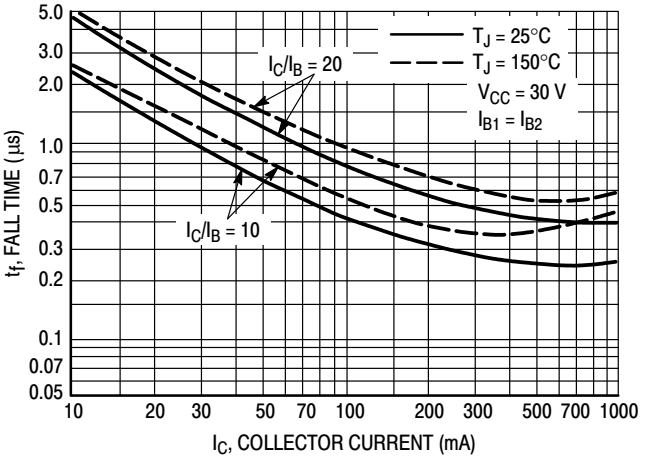


Figure 7. Fall Time

TYPICAL DC CHARACTERISTICS

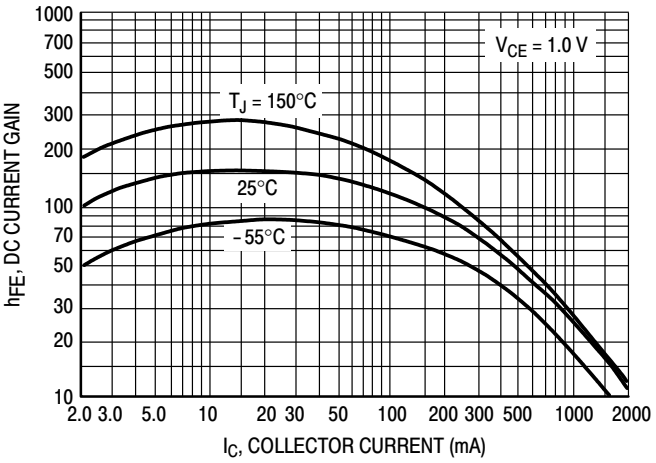


Figure 8. Current Gain

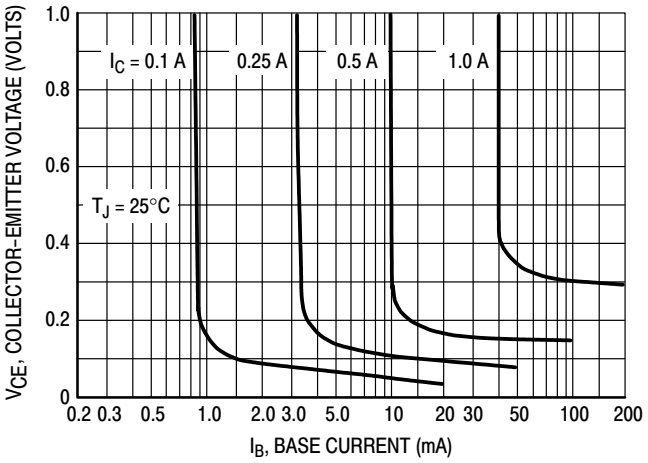


Figure 9. Collector Saturation Region

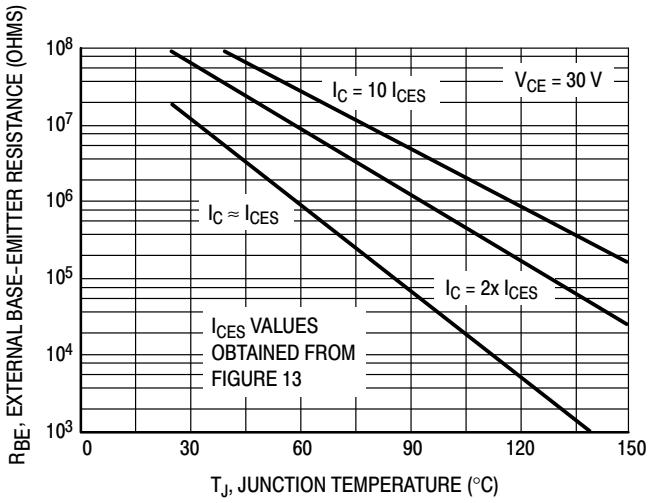


Figure 10. Effects of Base−Emitter Resistance

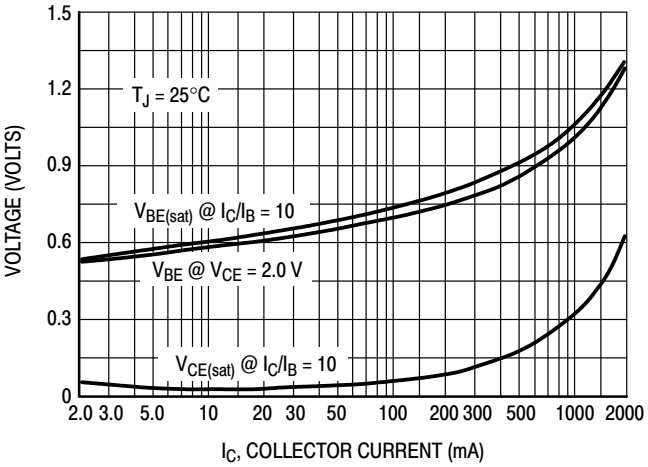


Figure 11. “On” Voltage

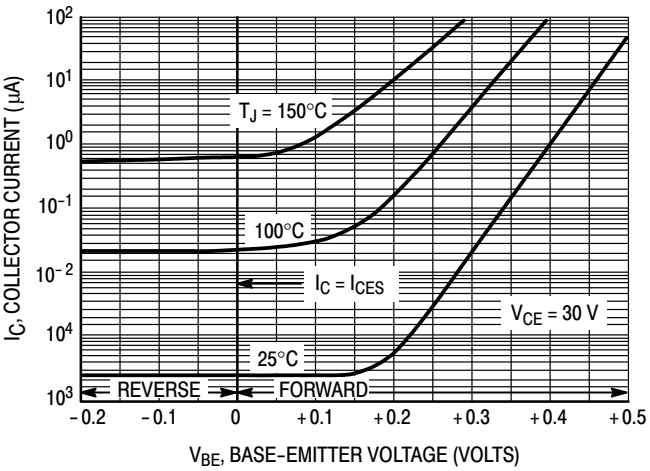


Figure 12. Collector Cut−Off Region

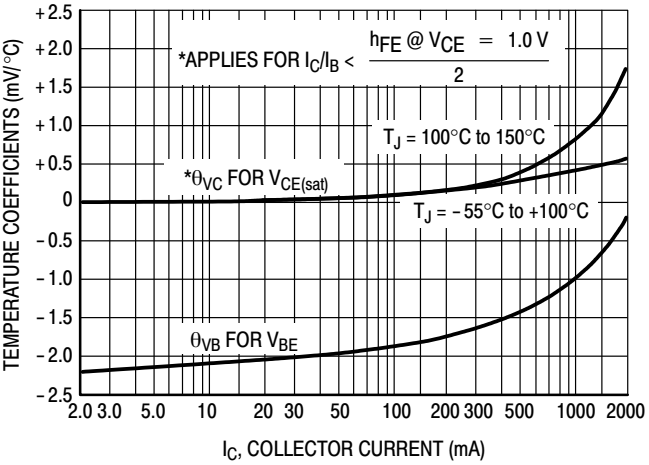
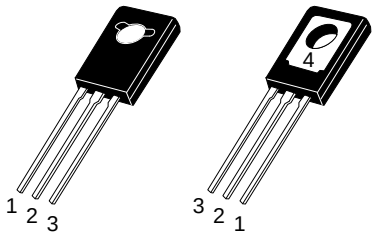


Figure 13. Temperature Coefficients

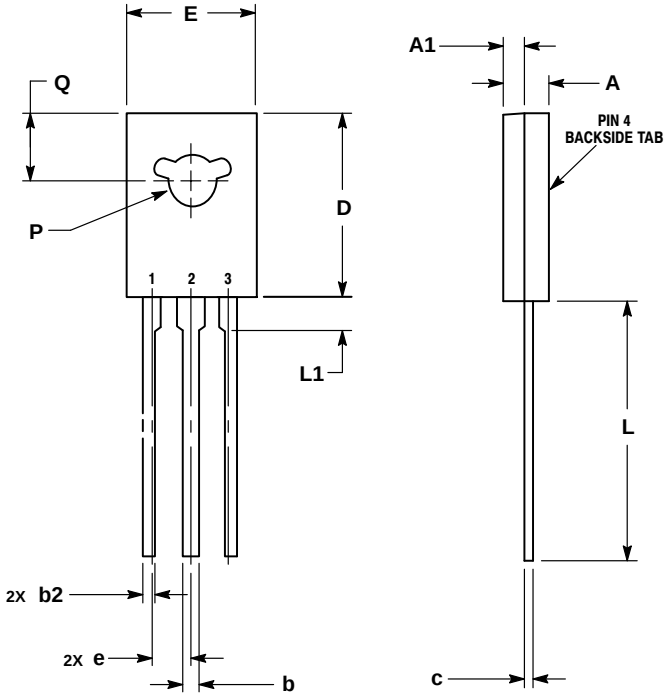
2N4920G

PACKAGE DIMENSIONS



FRONT VIEW BACK VIEW

TO−225
CASE 77−09
ISSUE AC



FRONT VIEW SIDE VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS	
DIM	MIN	MAX
A	2.40	3.00
A1	1.00	1.50
b	0.60	0.90
b2	0.51	0.88
c	0.39	0.63
D	10.60	11.10
E	7.40	7.80
e	2.04	2.54
L	14.50	16.63
L1	1.27	2.54
P	2.90	3.30
Q	3.80	4.20

STYLE 1:
PIN 1. EMITTER
2., 4. COLLECTOR
3. BASE

Thermopad is a trademark of Semiconductor Components Industries, LLC (SCILLC).

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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